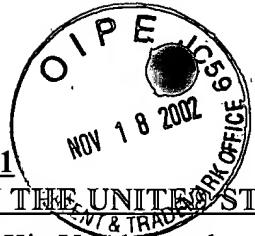


S/N 09/944,981



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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Walter L. Lindsay

Serial No.: 09/944,981

Group Art Unit: 2812

Filed: August 30, 2001

Docket: 1303.021US

Title: CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y203 AND
Gd203

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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on August 12, 2002. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect addition of new claims 61-63. The specific amendments to individual claims are detailed in the following marked up set of claims.

67. (New) A method of forming a transistor, comprising:

forming first and second source/drain regions;

forming a body region between the first and second source/drain regions;

evaporation depositing a metal layer on the body region, the metal being chosen from a group consisting of the group IIIIB elements and the rare earth series of the periodic table;

oxidizing the metal layer using a krypton(Kr)/oxygen (O₂) mixed plasma process to form a metal oxide layer on the body region; and

coupling a gate to the metal oxide layer.

68.

62. (New) The method of claim 61, wherein evaporation depositing the metal layer includes depositing a metal layer, the metal layer being chosen from a group consisting of yttrium and gadolinium.